

Amendments to the Claims:

The following listing will replace all prior listing of claims in the application.

Listing of Claims:

1. A Method of fabricating a die containing an integrated circuit comprising active components and passive components, characterized in that it comprises the method comprising:

[[-]]producing a first substrate (1) is produced containing at least one active component (3) of said active components and a second substrate (2) is produced containing [["]]critical[["]] passive components (7, 8) of said passive components; and
[[-]]bonding the two substrates (1) and (2) are bonded, wherein the bonding comprises performing a layer transfer through molecular adhesion, by layer transfer.

2. A Method according to claim 1, characterized in that wherein said at least one active component (3) comprises transistors.

3. A Method according to claim 1 or claim 2, characterized in that wherein said critical passive components comprise at least one capacitor (7) and/or at least one microelectromechanical system (MEMS) (8).

4. A method according to claim 1 wherein said critical passive components comprise at least one of one capacitor or at least one microelectromechanical system (MEMS).

54. A Method according to claim 3, characterized in that the wherein a dielectric material of said at least one capacitor (7) comprises is a perovskite.

65. A Method according to any one of claims 1, characterized in that wherein producing said second substrate (2) is comprises producing an electrically conductive material.

76. A Mmethod according to any one of claims 1, characterized in that wherein producing said second substrate (2) is comprises producing a dielectric material.

87. A Mmethod according to claim 7, characterized in that the wherein producing said second substrate (2) is of comprises producing perovskite.

98. A Mmethod according to any one of the preceding claims 8, further comprising producing characterized in that dielectric insulation trenches (6) are further produced in said second substrate during the production of said the second substrate (2).

109. A Mmethod according to any one of the preceding claims 9, further comprising producing characterized in that at least one non-critical passive component such as a capacitor in trenches (15) is further produced during the production of the said second substrate (2).

11. A method according to claim 9 wherein producing the non-critical passive component comprises producing a capacitor in trenches.

1012. A Mmethod according to any one of the preceding claims 9, further comprising producing characterized in that at least one inductor (12) in the vicinity of the a face of the second substrate (2) opposite the a bonding face is further produced after said bonding of the two substrates (1) and (2).

1311. A Mmethod according to claim 1012, characterized in that further comprising producing said at least one inductor (12) is produced on top of said inductive insulation trenches (18) previously formed produced in the said second substrate (2).

1214. A Mmethod according to any one of the preceding claims 12, further comprising producing characterized in that at least one interconnection line (16, 17) passing through all or part of the second substrate (2) is further produced after said bonding of the two said first and second substrates (1) and (2).

~~1315. A D_die (100) fabricated by a method according to any one of claims 1 to 123.~~

~~1416. A D_die (100) containing an integrated circuit comprising active components and passive components and consisting of including a single stack of layers, characterized in that whereinsaid die it comprises an interface between two of said layers such that the a said first portion of the die (100) situated on one side of said interface contains at least one active component of said active components and the other a second said portion of the said die (100) contains "critical" components (7, 8) of said passive components.~~

~~1517. A D_die according to claim 1614, characterized in that wherein said critical passive components comprise at least one capacitor (7) whose dielectric material is a perovskite and/or at least one MEMS (8) enclosed in a cavity (5) situated inside said die (100).~~

18. A die according to claim 16 wherein said critical passive components comprise at least one capacitor or at least one MEMS enclosed in a cavity situated inside said die.

19. A die according to claim 17 wherein the capacitor comprises a dielectric material comprising perovskite.

~~1620. A D_die according to claim 17 14 or claim 15, characterized in that it said die further comprises dielectric insulation trenches (6).~~

~~1721. A D_die according to any one of claims 18 14 to 16, characterized in that wherein said integrated circuit further comprises at least one non-critical passive component such as a capacitor in trenches (15).~~

22. A die according to claim 21 wherein said non-critical passive component comprises a capacitor in trenches.

~~1823. A D_die according to any one of claims 18 14 to 17, characterized in that wherein said active components (3) are disposed in the vicinity of a first face of the die~~

(100) and in that wherein said integrated circuit further comprises at least one inductor (12) situated in the a vicinity of the said face of the die (100) opposite said first face.

1924. A die according to claim 1822, characterized in that wherein said at least one inductor (12) is situated on top of inductive insulation trenches (18).

2025. A die according to any one of claims 14 to 19 21, characterized in that wherein said active components (3) are disposed in the a vicinity of a first face of the said die (100) and it said die further comprises at least one interconnection line (16, 17) that emerges in the vicinity of said face of said die (100) opposite said first face.

2025. A die according to any one of claims 14 to 19 21, characterized in that wherein said active components (3) are disposed in the a vicinity of a first face of the said die (100) and it said die further comprises at least one interconnection line (16, 17) that emerges in the vicinity of said face of said die (100) opposite said first face.